

8961726 TEXAS INSTR (OPTO)

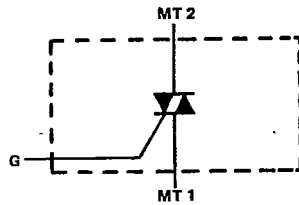
62C 36738 D

T-23-15
 SERIES TIC253, TIC263
 SILICON TRIACS

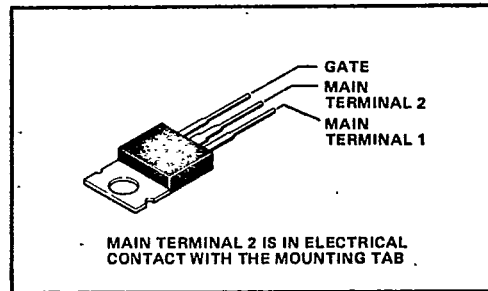
REVISED OCTOBER 1984

- High-Current Triacs
- 100 V to 800 V
- 12 A and 16 A RMS
- 100 A and 125 A Peak Current
- Max I_{GT} of 50 mA (Quadrants 1-3)

device schematic



TO-220AB PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	SUFFIX	SERIES	
		TIC253	TIC263
Repetitive peak off-state voltage, V_{DRM} (see Note 1)	A	100 V	100 V
	B	200 V	200 V
	C	300 V	300 V
	D	400 V	400 V
	E	500 V	500 V
	M	600 V	600 V
	S	700 V	700 V
	N	800 V	800 V
Full-cycle RMS on-state current at (or below) 70°C case temperature $I_T(RMS)$ (see Note 2)		20 A	25 A
Peak on-state surge current, full-sine-wave, I_{TSM} (see Note 3)		150 A	175 A
Peak gate current, I_{GM}		± 1 A	
Operating case temperature range		- 40°C to 110°C	
Storage temperature range		- 40°C to 110°C	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds		230°C	

4
TIC Devices

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 500 mW/°C for Series TIC253 and 625 mW/°C for Series TIC263.
 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) rated values of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

8961726 TEXAS INSTR (OPTO)

62C 36739 D

T-25-15

**SERIES TIC253, TIC263
SILICON TRIACS**

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SERIES TIC253			SERIES TIC263			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
I _{DRM}	Repetitive Peak Off-State Current V _{DRM} = Rated V _{DRM} , I _G = 0, T _C = 100°C	± 2			± 2			mA
I _{GT}	Peak Gate Trigger Current V _{supply} = + 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	7 50			7 50			mA
	V _{supply} = + 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	- 15 - 50			- 15 - 50			
	V _{supply} = - 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	- 16 - 50			- 16 - 50			
	V _{supply} = - 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	28			28			
V _{GTM}	Peak Gate Trigger Voltage V _{supply} = + 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	0.7 2			0.7 2			V
	V _{supply} = + 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	- 0.7 - 2			- 0.7 - 2			
	V _{supply} = - 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	- 0.8 - 2			- 0.8 - 2			
	V _{supply} = - 12 V [†] , R _L = 10 Ω, t _{w(g)} ≥ 20 μs	0.8 2			0.8 2			
V _{TM}	Peak On-State Voltage I _{TM} = ± 28.2 A, I _G = 50 mA, See Note 4	± 1.4 ± 1.7						V
	I _{TM} = ± 35.2 A, I _G = 50 mA, See Note 4				± 1.5 ± 1.7			
I _H	Holding Current V _{supply} = + 12 V [†] , I _G = 0, Initiating I _{TM} = 100 mA	6 40			6 40			mA
	V _{supply} = - 12 V [†] , I _G = 0, Initiating I _{TM} = - 100 mA	- 13 - 40			- 13 - 40			
I _L	Latching Current V _{supply} = + 12 V [†] , See Note 5	20			20			mA
	V _{supply} = - 12 V [†] , See Note 5	- 20			- 20			
dv/dt	Critical Rate of Rise of Off-State Voltage V _D = Rated V _D , I _G = 0, T _C = 110°C	450			450			V/μs
dv/dt (c)	Critical Rise of Commutation Voltage V _R = Rated V _D , di/dt = 0, T _C = 80°C	1			1			V/μs
di/dt	Critical Rate of Rise of On-State Current V _D = Rated V _D , I _{GT} = 50 mA, di _G /dt = 50 mA/μs, T _C = 110°C	200			200			A/μs

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, t_w ≤ 1 ms, duty cycle ≤ 2%. Voltage-sensing contacts, separate from the current-carrying contacts, are located within 3.2 mm (1/8 inch) from the device body.

7. The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: R_G = 100 Ω, t_w = 20 μs, t_r ≤ 15 ns, t_f ≤ 15 ns, f = 1 kHz.

thermal characteristics

PARAMETER	SERIES TIC253			SERIES TIC263			UNIT
	MIN	TYP	MAX	MIN	TYP	MAX	
R _{θJC}	1.52			1.22			°C/W
R _{θJA}	36			36			

4 TIC Devices

8961726 TEXAS INSTR (OPTO)

62C 36740 D

SERIES TIC253, TIC263
SILICON TRIACS

T-25-15

TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT
vs
CASE TEMPERATURE

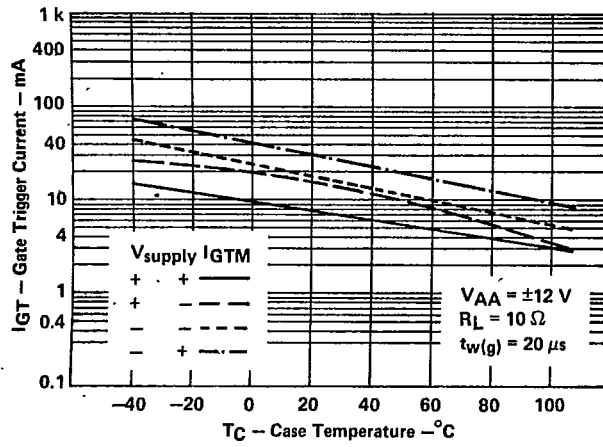


FIGURE 1

GATE TRIGGER VOLTAGE
vs
CASE TEMPERATURE

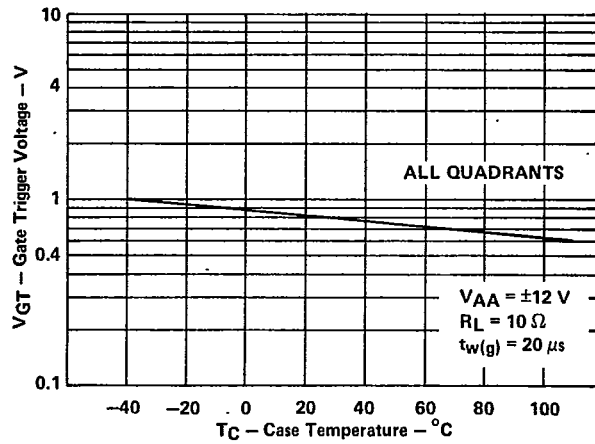


FIGURE 2

4

TIC Devices

8961726 TEXAS INSTR (OPTO)

62C 36741 D

SERIES TIC253, TIC263
SILICON TRIACS

7-25-15

TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

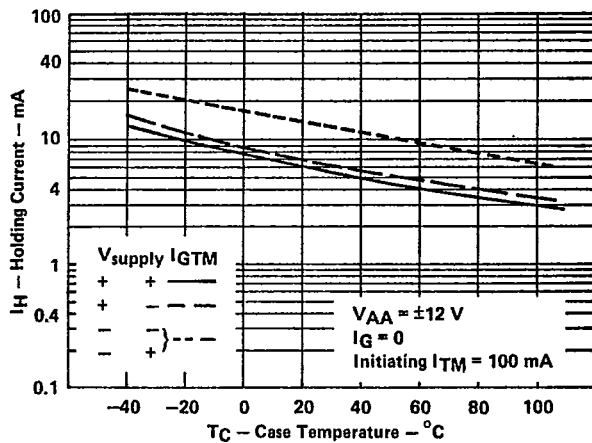


FIGURE 3

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

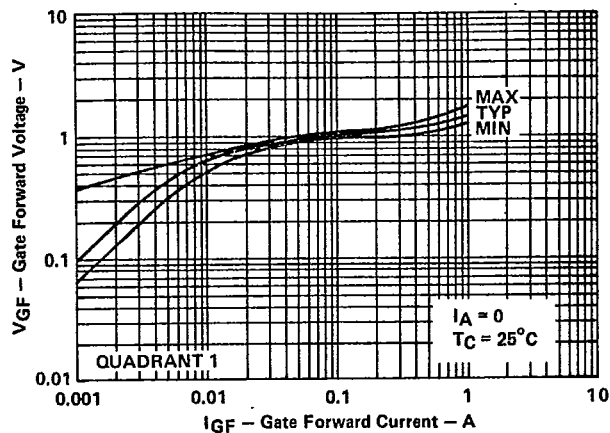


FIGURE 4

4

TIC Devices

8961726 TEXAS INSTR (OPTO)

62C 36742 D

SERIES TIC253, TIC263
SILICON TRIACS

T-25-15

TYPICAL CHARACTERISTICS

LATCHING CURRENT
vs
CASE TEMPERATURE

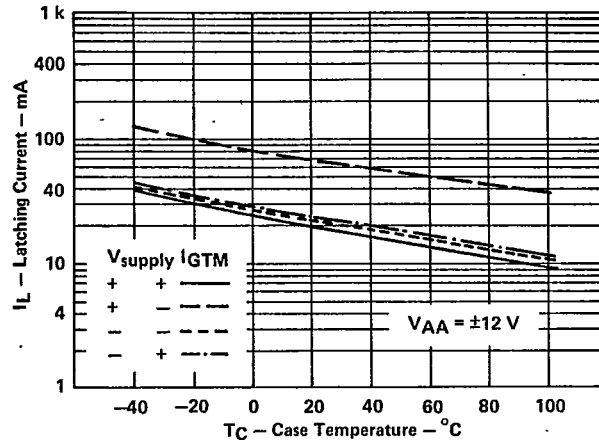


FIGURE 5

4

TIC Devices

TEXAS INSTRUMENTS

POST OFFICE BOX 225012 • DALLAS, TEXAS 75265